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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/472,757	12/27/1999	ROBERT J. O'DONNELL	LAM133/P0582	9169

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EXAMINER
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UMEZ ERONINI, LYNETTE T

ART UNIT	PAPER NUMBER
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1765

DATE MAILED: 04/25/2003

16

Please find below and/or attached an Office communication concerning this application or proceeding.

<b>Office Action Summary</b>	Application No. 09/472,757	Applicant(s) O DONNELL, ROBERT J.	
	Examiner Lynette T. Umez-Eronini	Art Unit 1765	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

### Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

### Status

- 1) ☐ Responsive to communication(s) filed on 27 February 2003.
- 2a) ☒ This action is **FINAL**.                      2b) ☐ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

### Disposition of Claims

- 4) ☒ Claim(s) 1-15 and 17-20 is/are pending in the application.
- 4a) Of the above claim(s) 20 is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-15 and 18 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☒ Claim(s) 17 and 19 are subject to restriction and/or election requirement.

### Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on \_\_\_\_\_ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.  
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.  
If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

### Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).  
a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
  2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
  3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).  
a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

### Attachment(s)

- |  |   |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892)                             | 4) <input type="checkbox"/> Interview Summary (PTO-413) Paper No(s). _____  |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948)         | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449) Paper No(s) _____ | 6) <input type="checkbox"/> Other:  |

## DETAILED ACTION

This communication is in response to Applicant's request to withdraw the finality of the Office Action and concomitant amendment of January 2, 2003. Pursuant to applicant's request, the finality of the rejection of date of last office action has been withdrawn. It is noted that the rejection itself was not withdrawn. Applicant's amendment of January 2, 2003 has been treated as a response to a non-final office action and entered. The rejection is repeated.

### ***Claim Rejections - 35 USC § 112***

1. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

2. Claims 17, 19 and 20 are rejected under 35 U.S.C. 112, first paragraph, as containing subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention.

In claim 17, lines 1-3, "wherein the stripping away the etch mask and removing some residual sidewall passivation, simultaneously strips away the etch mask and removes parts of the metal-containing layer that are redeposited to form residual sidewall passivation" lacks support for simultaneously stripping away the etch mask and

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removing parts of the metal-containing layer that are redeposited to form residual sidewall passivation, as disclosed in the Specification.

In claim 19, lines 1-3, "wherein the stripping away the etch mask and removing some residual sidewall passivation comprises removing metal containing parts of the metal-containing layer that are redeposited to form residual sidewall passivation" lacks support for removing metal containing parts of the metal-containing layer that are redeposited to form residual sidewall passivation, as disclosed in the Specification (page 4, lines 23-25).

In claim 20, lines 1-3, "wherein the stripping away the etch mask and removing some residual sidewall passivation, simultaneously strips away the etch mask and removes the residual sidewall passivation" lacks support for simultaneously stripping away the etch mask and removing the residual sidewall passivation, as disclosed in the Specification (page 4, lines 23-25).

### ***Claim Rejections - 35 USC § 102***

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

4. Claims 1, 15, and 18 are rejected under 35 U.S.C. 102(b) as being anticipated by Hsieh et al. (US 5,776,832).

Hsieh teaches applying a photoresist to a substrate, which is exposed through an etch mask **20** and forming the etch mask over portions of a metal layer **18** where the metal conducting lines are desired (column 4, line 60 – column 5, line 2), which reads on, a method for etching partially through a metal-containing layer disposed above a substrate, wherein part of the said metal-containing layer is disposed below an etch mask and part of the said metal-containing layer is not disposed below the etch mask.

The method comprises:

anisotropically plasma etching the metal layer in a reactive ion etcher (column 5, lines 9-17) by using a chlorine-containing gas or gas mixtures such as  $\text{BCl}_3$  and  $\text{Cl}_2$ , which results in the formation of  $\text{AlCl}_3$  on the Al sidewalls (same as applicant's residual sidewall passivation), (column 3, lines 9-13) and metal side wall polymer (column 3, lines 24-26) reads on the method comprises the steps of:

placing the substrate in an etch chamber;

flowing and etchant gas into the etch chamber;

creating a plasma from the etchant gas in the etch chamber; and

etching away parts of the metal-containing layer not disposed below the etch masks, wherein some of the etched away parts of the metal-containing layer is redeposited to form residual sidewall passivation while the substrate is in the etch chamber.

Table 1 shows the etching flow rate and time of the etching gases are set at zero when oxygen ashing is being carried out (column 5, lines 29-48), which reads on,

discontinuing the flow of the etchant gas into the etch chamber.

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In situ oxygen plasma ashing is carried out in the same etching chamber after etching the metal lines and prior to removing the wafers (column 3, lines 16-19) and under pressure using pure oxygen and at a flow rate as specified in Table 1 (column 5, lines 53-56). This in-situ oxygen ashing in the same etching chamber passivates the aluminum sidewalls by reducing chlorine on the aluminum sidewalls with oxygen and partially strips the photoresist (column 3, lines 17-21 and 24-25), which reads on:

flowing the etch mask stripping gas in the etch chamber;  
creating a plasma from the etch mask stripping gas into the etch chamber; and  
stripping away the etch mask and removing some residual sidewall passivation, while the substrate is in the etch chamber; and  
removing the substrate from the etch chamber.

It is noted that Hsieh method of ashing the aluminum sidewalls (same as applicant's residual sidewall passivation), passivates the layer by reducing chlorine on the aluminum sidewalls with oxygen, which would result in a passivated (aluminum oxide) layer which free of  $\text{AlCl}_3$  and thereby read on removing some residual sidewall passivation.

### ***Claim Rejections - 35 USC § 103***

5. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

6. Claims 2-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hsieh (US '832) as applied to claim 1 above, in view of applicant's admitted prior art and Fukuyama et al. (US 5,770,100) and further in view of Tepman et al. (US 5,186,718).

Hsieh differs in failing to teach:

electrostatically attracting the plasma from the etch mask stripping gas to the substrate in the etch chamber, **in claim 2.**

Applicant's admitted prior art teaches reactive ion metal etch chambers, in which the wafer is biased to create a potential across the wafer to electrostatically attract the plasma to wafer (Specification page 1, lines 27-30), which reads on electrostatically attracting the plasma from any gas as well as an etch mask stripping gas to the substrate in the etch chamber, as in the claimed invention.

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh by biasing a wafer to electrostatically attract the plasma as taught by the admitted prior art for the purpose of enhancing the etching of the wafer (Specification, page 1, line 30).

Hsieh in view of applicant's admitted prior art differs in failing to teach:

placing the substrate in and removing the substrate from a load lock, **in claim 6** and

placing the substrate into a corrosion passivation chamber after the substrate has been removed from the etch chamber, and exposing the wafer to a non-plasma high temperature water vapor, **in claim 7.**

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Fukuyama teaches an anticorrosion treatment using a load lock system (Figure 1) to transfer a wafer from an etching chamber to a post-etch treatment chamber 8, where anticorrosion treatment of sample is carried out using vaporized gas of water (column 3, line 61 – column 4, line 21 and column 8, lines 41-54).

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh in view of the admitted prior art by moving and removing the substrate from a load lock, placing a sample into a corrosion passivation chamber after the substrate has been removed from the etch chamber and carrying out the anticorrosion passivation in as taught by Fukuyama for the purpose of preventing contamination in the processing chamber.

Hsieh in view of applicant's admitted prior art and in view of Fukuyama differs in failing to teach: transferring the substrate from the corrosion passivation chamber to a cooling station; cooling the substrate in the cooling station; and transferring the substrate from the cooling station to the load lock, **in claim 8**.

Tepman teaches using the load lock system for transferring wafers and using either post etching chamber 26 and 27 for cooling wafers following treating in a processing chambers 34 (column 4, lines 23-29). It is noted that the processing chambers 34 is not limited to only etching and ashing. Other processes such as anti-corrosion treatment can be performed in chambers 34.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh in view of applicant's admitted prior art and in



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view of Fukuyama by using a load lock system to transfer a substrate from a processing chamber to a cooling station and to a load lock as taught by Tepman for the purpose of preventing contamination in the processing chamber.

Hsieh in view of applicant's admitted prior art and in view of Fukuyama and further in and Tepman differs in failing to specify processing variables such as the etchant pressure of 1 and 80 millitorr during the stripping step, as recited in **claims 9 and 12** and a bias power between -10 and -1000 volts during the step of electrostatically attracting the plasma from the etchant gas and the stripping gas, **as in claims 11 and 14**; and the substrate at a temperature between 10 and 100° C, **as in claims 10 and 13**.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh in view of applicant's admitted prior art and in view of Fukuyama and further in view of Tepman by employing any of a variety of operational variables such as temperature and pressure as claimed by the applicant, since it has been held that discovering an optimum value of a result effective variable involves only routine skill in the art. In re Boesch, 617, F.2d 272, 205 USPQ 215 (CCPA 1980).

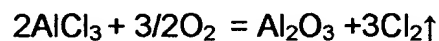
### ***Response to Arguments***

7. Applicant's arguments filed October 9, 20002 have been fully considered but they are not persuasive. Applicant argues that Hsieh teaches the oxygen ashing step strips

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photoresist and build up sidewall passivation (column 3, lines 19-24 and column 6, lines 35-41) and thereby fails to teach removing some residual sidewall passivation, but instead adds more sidewall passivation.

Applicant argument is unpersuasive because applicant's "sidewall passivation" is "redeposited etch residue, which may be aluminum in the form of chloride or fluoride" Specification, lines 18-20), which is the same as the "formation of  $\text{AlCl}_3$  on the Al sidewall" material that results from etching a metal-containing layer (column 3, lines 8-13), as taught by Hsieh and which is claimed in the present invention and which is by "Insitu oxygen ashing in the same etching chamber to passivates the aluminum sidewalls by reducing the chlorine on the aluminum sidewalls with oxygen and further form a non-volatile deposition on the sidewalls to passivate the surface . . ." Assuming the following reaction,



to depict  $\text{AlCl}_3$  on the Al sidewall that is oxygen ashed, then one can assume that the non-volatile deposition on the sidewalls is  $\text{Al}_2\text{O}_3$ , which differs from applicant's "residual sidewall passivation." Hence, the aforementioned reads on removing some residual sidewall passivation, as in the claimed invention.

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In response to applicant's amendment of Paper No. 14, filed February 27, 2003 is the following Office Action.

***Election/Restrictions***

8. Newly submitted claims 17 and 19 are directed to an invention that is independent or distinct from the invention originally claimed for the following reasons: (Twice Amended) Claim 17 is drawn to an apparatus and (Once Amended) claim 19 is drawn to a semiconductor chip, which differs from the originally presented invention that is drawn to an etching method.

Since applicant has received an action on the merits for the originally presented invention, this invention has been constructively elected by original presentation for prosecution on the merits. Accordingly, claims 17 and 19 are withdrawn from consideration as being directed to a non-elected invention. See 37 CFR 1.142(b) and MPEP § 821.03.

***Claim Rejections - 35 USC § 102***

9. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless –

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

10. Claims 1, 15, and 18 are rejected under 35 U.S.C. 102(b) as being anticipated by Hsieh et al. (US 5,776,832).

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Hsieh teaches applying a photoresist to a substrate, which is exposed through an etch mask **20** and forming the etch mask over portions of a metal layer **18** where the metal conducting lines are desired (column 4, line 60 – column 5, line 2), which reads on, a method for etching partially through a metal-containing layer disposed above a substrate, wherein part of the said metal-containing layer is disposed below an etch mask and part of the said metal-containing layer is not disposed below the etch mask.

The method comprises:

anisotropically plasma etching the metal layer in a reactive ion etcher (column 5, lines 9-17) by using a chlorine-containing gas or gas mixtures such as  $\text{BCl}_3$  and  $\text{Cl}_2$ , which results in the formation of  $\text{AlCl}_3$  on the Al sidewalls (same as applicant's residual sidewall passivation), (column 3, lines 9-13) and metal side wall polymer (column 3, lines 24-26) reads on the method comprises the steps of:

placing the substrate in an etch chamber, **as in claims 1 and 15**;

flowing and etchant gas into the etch chamber, **as in claim 1**;

creating a plasma from the etchant gas in the etch chamber **as in claim 1**; and

etching away parts of the metal-containing layer not disposed below the etch masks, wherein some of the etched away parts of the metal-containing layer is redeposited to form residual sidewall passivation while the substrate is in the etch chamber, **as in claim 15**.

Table 1 shows the etching flow rate and time of the etching gases are set at zero when oxygen ashing is being carried out (column 5, lines 29-48), which reads on,

discontinuing the flow of the etchant gas into the etch chamber, **as in claim 1**.

In situ oxygen plasma ashing is carried out in the same etching chamber after etching the metal lines and prior to removing the wafers (column 3, lines 16-19) and under pressure using pure oxygen and at a flow rate as specified in Table 1 (column 5, lines 53-56). This in-situ oxygen ashing in the same etching chamber passivates the aluminum sidewalls by reducing chlorine on the aluminum sidewalls with oxygen and partially strips the photoresist (column 3, lines 17-21 and 24-25), which reads on:

flowing the etch mask stripping gas in the etch chamber **as in claim 1**;

creating a plasma from the etch mask stripping gas into the etch chamber **in claim 1**; and

stripping away the etch mask and removing most of the residual sidewall passivation, while the substrate is in the etch chamber, wherein plasma created by the etch mask stripping gas strips away the etch mask and removes most of the residual sidewall passivation, **as in claim 1** and using a stripping gas to strip away the etch mask and remove most of the sidewall passivation while the substrate is in the etch chamber, **as in claim 15**; and

removing the substrate from the etch chamber, **as in claims 1 and 15**; and

Since Hsieh uses the same stripping method as that of the claimed invention, the using Hsieh's method of stripping away comprises accelerating oxygen plasma to the substrate which would inherently remove parts of the metal-containing layer that are redeposited to form residual sidewall passivation, **as in claim 18**.

***Claim Rejections - 35 USC § 103***

11. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

12. Claims 2-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Hsieh (US '832) as applied to claim 1 above, in view of applicant's admitted prior art and Fukuyama et al. (US 5,770,100) and further in view of Tepman et al. (US 5,186,718).

Hsieh differs in failing to teach:

electrostatically attracting the plasma from the etch mask stripping gas to the substrate in the etch chamber, **in claim 2**.

Applicant's admitted prior art teaches reactive ion metal etch chambers, in which the wafer is biased to create a potential across the wafer to electrostatically attract the plasma to wafer (Specification page 1, lines 27-30), which reads on electrostatically attracting the plasma from any gas as well as an etch mask stripping gas to the substrate in the etch chamber, as in the claimed invention.

It is the examiner's position that it would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh by biasing a wafer to electrostatically attract the plasma as taught by the admitted prior art for the purpose of enhancing the etching of the wafer (Specification, page 1, line 30).

Hsieh in view of applicant's admitted prior art differs in failing to teach:

placing the substrate in and removing the substrate from a load lock, **in claim 6** and

placing the substrate into a corrosion passivation chamber after the substrate has been removed from the etch chamber, and exposing the wafer to a non-plasma high temperature water vapor, **in claim 7**.

Fukuyama teaches an anticorrosion treatment using a load lock system (Figure 1) to transfer a wafer from an etching chamber to a post-etch treatment chamber **8**, where anticorrosion treatment of sample is carried out using vaporized gas of water (column 3, line 61 – column 4, line 21 and column 8, lines 41-54).

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh in view of the admitted prior art by moving and removing the substrate from a load lock, placing a sample into a corrosion passivation chamber after the substrate has been removed from the etch chamber and carrying out the anticorrosion passivation in as taught by Fukuyama for the purpose of preventing contamination in the processing chamber.

Hsieh in view of applicant's admitted prior art and in view of Fukuyama differs in failing to teach: transferring the substrate from the corrosion passivation chamber to a cooling station; cooling the substrate in the cooling station; and transferring the substrate from the cooling station to the load lock, **in claim 8**.

Tepman teaches using the load lock system for transferring wafers and using either post etching chamber **26** and **27** for cooling wafers following treating in a

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processing chambers **34** (column 4, lines 23-29). It is noted that the processing chambers **34** is not limited to only etching and ashing. Other processes such as anti-corrosion treatment can be performed in chambers **34**.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh in view of applicant's admitted prior art and in view of Fukuyama by using a load lock system to transfer a substrate from a processing chamber to a cooling station and to a load lock as taught by Tepman for the purpose of preventing contamination in the processing chamber.

Hsieh in view of applicant's admitted prior art and in view of Fukuyama and further in and Tepman differs in failing to specify processing variables such as the etchant pressure of 1 and 80 millitorr during the stripping step, as recited in **claims 9 and 12** and a bias power between -10 and -1000 volts during the step of electrostatically attracting the plasma from the etchant gas and the stripping gas, **as in claims 11 and 14**; and the substrate at a temperature between 10 and 100° C, **as in claims 10 and 13**.

It would have been obvious to one having ordinary skill in the art at the time of the claimed invention to modify Hsieh in view of applicant's admitted prior art and in view of Fukuyama and further in view of Tepman by employing any of a variety of operational variables such as temperature and pressure as claimed by the applicant, since it has been held that discovering an optimum value of a result effective variable



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involves only routine skill in the art. In re Boesch, 617, F.2d 272, 205 USPQ 215 (CCPA 1980).

### ***Response to Arguments***

13. Applicant's arguments filed February 27, 2003 have been fully considered but they are not persuasive. Applicant traverses the 103 rejection of claims 2-14 as being unpatentable over Hsieh (US '832) in view of applicant's admitted prior art. Applicant argues that the admitted prior art fails to teach applying an electrostatic bias during stripping, since the admitted prior art stated that such stripping outside of the etch chamber in a strip chamber.

Applicant's argument is unpersuasive because the admitted prior art is relied upon to teach Hsieh's deficiency, electrostatically attracting the plasma from the etch mask stripping gas to the substrate in the etch chamber. Applicant's admitted prior art teaches reactive ion metal etch chambers, in which the wafer is biased to create a potential across the wafer to electrostatically attract the plasma to wafer (Specification page 1, lines 27-30), which reads on electrostatically attracting the plasma from any gas as well as an etch mask stripping gas to the substrate in the etch chamber, which would read on applicant's strip chamber.

### ***Conclusion***

14. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP

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§ 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire **THREE MONTHS** from the mailing date of this action. In the event a first reply is filed within **TWO MONTHS** of the mailing date of this final action and the advisory action is not mailed until after the end of the **THREE-MONTH** shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than **SIX MONTHS** from the date of this final action.

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lynette T. Umez-Eronini whose telephone number is 703-306-9074. The examiner is normally unavailable on the First Friday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Benjamin Utech can be reached on 703-308-3836. The fax phone numbers for the organization where this application or proceeding is assigned are 703-972-9310 for regular communications and 703-972-9311 for After Final communications.

ltue  
April 24, 2003

  
BENJAMIN L. UTECH  
SUPERVISORY PATENT EXAMINER  
TECHNOLOGY CENTER 1700